

**RADIATION HARDENED
POWER MOSFET
THRU-HOLE (Low-Ohmic TO-254AA)**

100V, P-CHANNEL
REF: MIL-PRF-19500/713
R5 TECHNOLOGY

Product Summary

Part Number	Radiation Level	RDS(on)	I _D	QPL Part Number
IRHMS597160	100 kRads(Si)	0.05Ω	-45A	JANSR2N7550T1
IRHMS593160	300 kRads(Si)	0.05Ω	-45A	JANSF2N7550T1



Description

IR HiRel R5 technology provides high performance power MOSFETs for space applications. These devices have been characterized for Single Event Effects (SEE) with useful performance up to an LET of 80 (MeV/(mg/cm²)). The combination of low RDS(on) and low gate charge reduces the power losses in switching applications such as DC to DC converters and motor control. These devices retain all of the well established advantages of MOSFETs such as voltage control, fast switching and temperature stability of electrical parameters.

Features

- Single Event Effect (SEE) Hardened
- Identical Pre- and Post-Electrical Test Conditions
- Repetitive Avalanche Ratings
- Dynamic dv/dt Ratings
- Simple Drive Requirements
- Hermetically Sealed
- Electrically Isolated
- Ceramic Eyelets
- Light Weight
- High Electrical Conductive Package
- ESD Rating: Class 3A per MIL-STD-750, Method 1020

Absolute Maximum Ratings

Pre-Irradiation

Symbol	Parameter	Value	Units
I _{D1} @ V _{GS} = -12V, T _C = 25°C	Continuous Drain Current	-45	A
I _{D2} @ V _{GS} = -12V, T _C = 100°C	Continuous Drain Current	-28.5	
I _{DM} @ T _C = 25°C	Pulsed Drain Current ①	-180	
P _D @ T _C = 25°C	Maximum Power Dissipation	208	W
	Linear Derating Factor	1.67	W/°C
V _{GS}	Gate-to-Source Voltage	± 20	V
E _{AS}	Single Pulse Avalanche Energy ②	480	mJ
I _{AR}	Avalanche Current ①	-45	A
E _{AR}	Repetitive Avalanche Energy ①	20.8	mJ
dv/dt	Peak Diode Recovery dv/dt ③	-6.0	V/ns
T _J T _{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C
	Lead Temperature	300 ((0.063in./1.6mm from case for 10s)	
	Weight	9.3 (Typical)	g

For Footnotes, refer to the page 2.

Electrical Characteristics @ T_J = 25°C (Unless Otherwise Specified)

Pre-Irradiation

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
BV _{DSS}	Drain-to-Source Breakdown Voltage	-100	—	—	V	V _{GS} = 0V, I _D = -1.0mA
ΔBV _{DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	-0.13	—	V/°C	Reference to 25°C, I _D = -1.0mA
R _{DS(on)}	Static Drain-to-Source On-State Resistance	—	—	0.05	Ω	V _{GS} = -12V, I _{D2} = -28.5A ④
V _{GS(th)}	Gate Threshold Voltage	-2.0	—	-4.0	V	V _{DS} = V _{GS} , I _D = -1.0mA
G _{fs}	Forward Transconductance	24	—	—	S	V _{DS} = -15V, I _{D2} = -28.5A ④
I _{DSS}	Zero Gate Voltage Drain Current	—	—	-10	μA	V _{DS} = -80V, V _{GS} = 0V
		—	—	-25		V _{DS} = -80V, V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Leakage Forward	—	—	-100	nA	V _{GS} = -20V
	Gate-to-Source Leakage Reverse	—	—	100		V _{GS} = 20V
Q _G	Total Gate Charge	—	—	170	nC	I _{D1} = -45A
Q _{GS}	Gate-to-Source Charge	—	—	65		V _{DS} = -50V
Q _{GD}	Gate-to-Drain ('Miller') Charge	—	—	30		V _{GS} = -12V
t _{d(on)}	Turn-On Delay Time	—	—	35	ns	V _{DD} = -50V
t _r	Rise Time	—	—	100		I _{D1} = -45A
t _{d(off)}	Turn-Off Delay Time	—	—	100		R _G = 1.20Ω
t _f	Fall Time	—	—	120		V _{GS} = -12V
L _S + L _D	Total Inductance	—	6.8	—	nH	Measured from Drain lead (6mm /0.25in. from package) to Source lead (6mm /0.25in. from package) with Source wires internally bonded from Source Pin to Drain Pad
C _{iSS}	Input Capacitance	—	6110	—	pF	V _{GS} = 0V
C _{oSS}	Output Capacitance	—	1574	—		V _{DS} = -25V
C _{rSS}	Reverse Transfer Capacitance	—	115	—		f = 1.0MHz

Source-Drain Diode Ratings and Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I _S	Continuous Source Current (Body Diode)	—	—	-45	A	
I _{SM}	Pulsed Source Current (Body Diode) ①	—	—	-180		
V _{SD}	Diode Forward Voltage	—	—	-5.0	V	T _J = 25°C, I _S = -45A, V _{GS} = 0V ④
t _{rr}	Reverse Recovery Time	—	—	200	ns	T _J = 25°C, I _F = -45A, V _{DD} ≤ -50V
Q _{rr}	Reverse Recovery Charge	—	—	1.6	μC	di/dt = 100A/μs ④
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L _S +L _D)				

Thermal Resistance

Symbol	Parameter	Min.	Typ.	Max.	Units
R _{θJC}	Junction-to-Case	—	—	0.60	°C/W
R _{θJCS}	Case -to- Sink	—	0.21	—	
R _{θJA}	Junction-to-Ambient (Typical socket mount)	—	—	48	

Footnotes:

- ① Repetitive Rating; Pulse width limited by maximum junction temperature.
- ② V_{DD} = -50V, starting T_J = 25°C, L = 0.48mH, Peak I_L = -45A, V_{GS} = -12V
- ③ I_{SD} ≤ -45A, di/dt ≤ -365A/μs, V_{DD} ≤ -100V, T_J ≤ 150°C
- ④ Pulse width ≤ 300 μs; Duty Cycle ≤ 2%
- ⑤ Total Dose Irradiation with V_{GS} Bias. -12 volt V_{GS} applied and V_{DS} = 0 during irradiation per MIL-STD-750, Method 1019, condition A.
- ⑥ Total Dose Irradiation with V_{DS} Bias. -80 volt V_{DS} applied and V_{GS} = 0 during irradiation per MIL-STD-750, Method 1019, condition A.

Radiation Characteristics

IR HiRel radiation hardened MOSFETs are tested to verify their radiation hardness capability. The hardness assurance program at IR HiRel is comprised of two radiation environments. Every manufacturing lot is tested for total ionizing dose (per notes 5 and 6) using the TO-3 package. Both pre- and post-irradiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison.

Table1. Electrical Characteristics @ Tj = 25°C, Post Total Dose Irradiation ⑤⑥

Symbol	Parameter	100 kRads (Si) ¹		300 kRads (Si) ²		Units	Test Conditions
		Min.	Max.	Min.	Max.		
BV _{DSS}	Drain-to-Source Breakdown Voltage	-100	—	-100	—	V	V _{GS} = 0V, I _D = -1.0mA
V _{GS(th)}	Gate Threshold Voltage	-2.0	-4.0	-2.0	-5.0	V	V _{DS} = V _{GS} , I _D = -1.0mA
I _{GSS}	Gate-to-Source Leakage Forward	—	-100	—	-100	nA	V _{GS} = -20V
I _{GSS}	Gate-to-Source Leakage Reverse	—	100	—	100	nA	V _{GS} = 20V
I _{DSS}	Zero Gate Voltage Drain Current	—	-10	—	-10	μA	V _{DS} = -80V, V _{GS} = 0V
R _{DS(on)}	Static Drain-to-Source ④ On-State Resistance (TO-3)	—	0.05	—	0.05	Ω	V _{GS} = -12V, I _{D2} = -28.5A
R _{DS(on)}	Static Drain-to-Source ④ On-State Resistance (TO-254AA)	—	0.05	—	0.05	Ω	V _{GS} = -12V, I _{D2} = -28.5A
V _{SD}	Diode Forward Voltage	—	-5.0	—	-5.0	V	V _{GS} = 0V, I _S = -45A

1. Part number IRHMS597160 (JANSR2N7550T1)
2. Part numbers IRHMS593160 (JANSF2N7550T1)

IR HiRel radiation hardened MOSFETs have been characterized in heavy ion environment for Single Event Effects (SEE). Single Event Effects characterization is illustrated in Fig. a and Table 2.

Table 2. Typical Single Event Effect Safe Operating Area

LET (MeV/(mg/cm ²))	Energy (MeV)	Range (μm)	VDS (V)				
			@VGS=0V	@VGS=5V	@VGS=10V	@VGS=15V	@VGS=20V
38 ± 5%	270 ± 7.5%	35 ± 7.5%	-100	-100	-100	-100	-100
61 ± 5%	330 ± 7.5%	31 ± 7.5%	-100	-100	-100	-100	-25
84 ± 5%	350 ± 10%	28 ± 7.5%	-100	-100	-100	-30	—

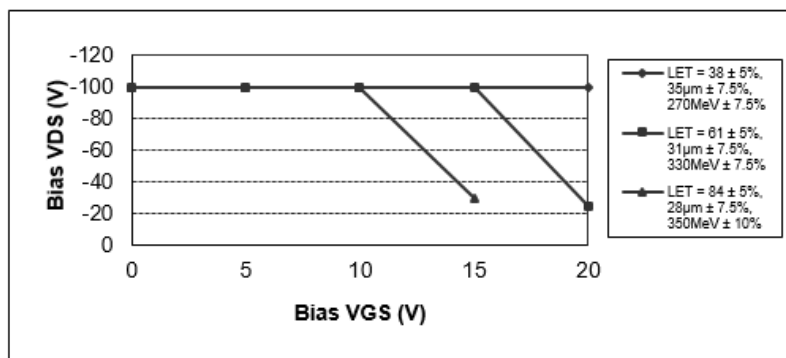


Fig a. Typical Single Event Effect, Safe Operating Area

For Footnotes, refer to the page 2.

Pre-Irradiation

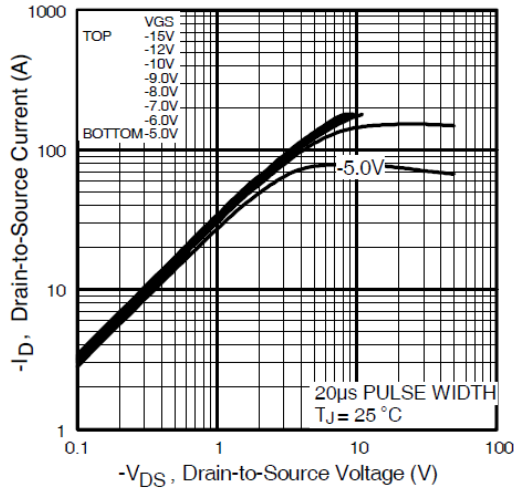


Fig 1. Typical Output Characteristics

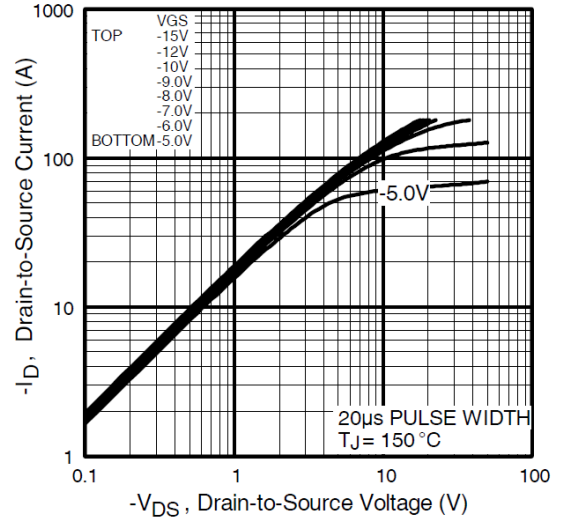


Fig 2. Typical Output Characteristics

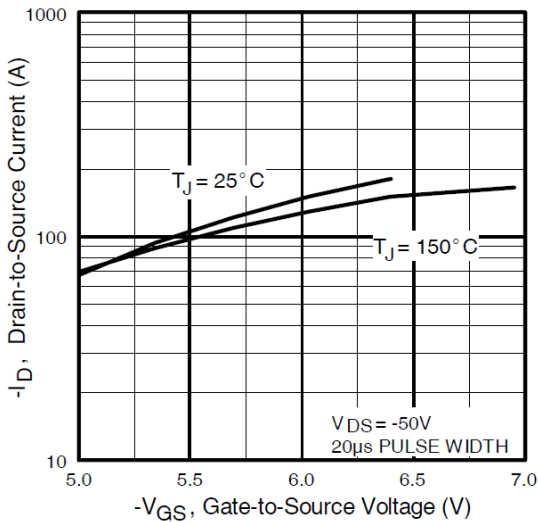


Fig 3. Typical Transfer Characteristics

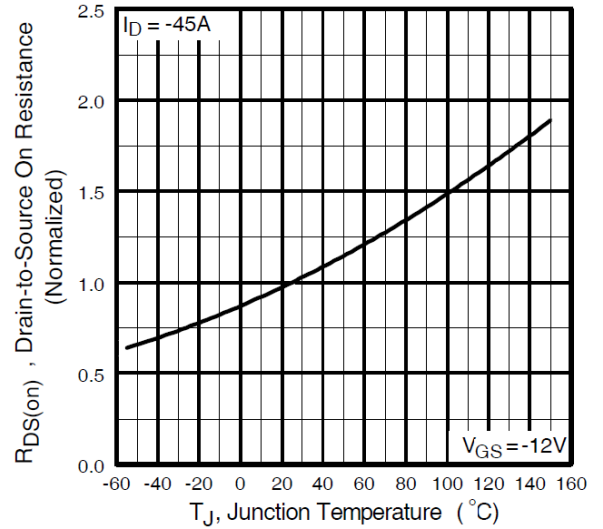


Fig 4. Normalized On-Resistance Vs. Temperature

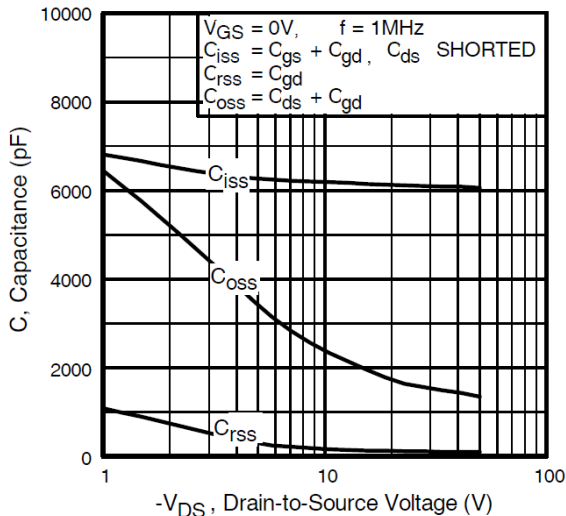


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

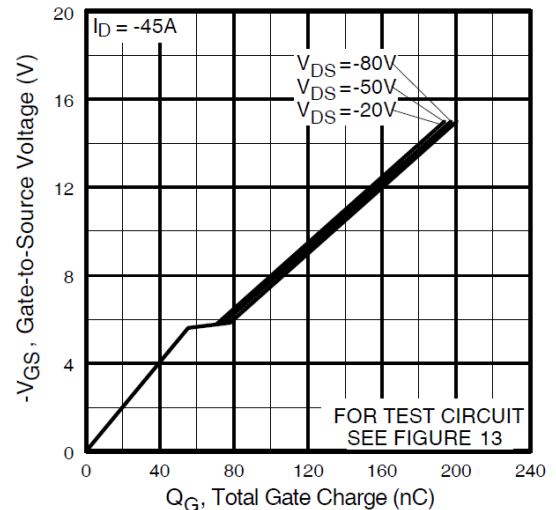


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

Pre-Irradiation

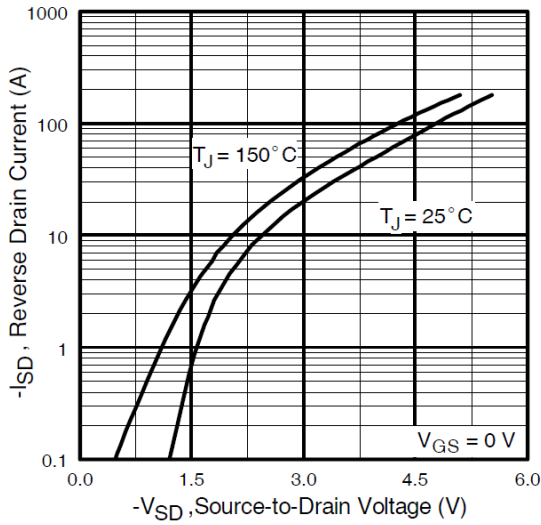


Fig 7. Typical Source-Drain Diode Forward Voltage

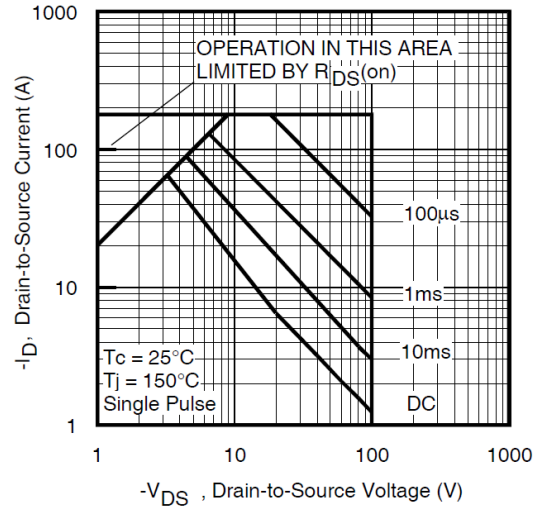


Fig 8. Maximum Safe Operating Area

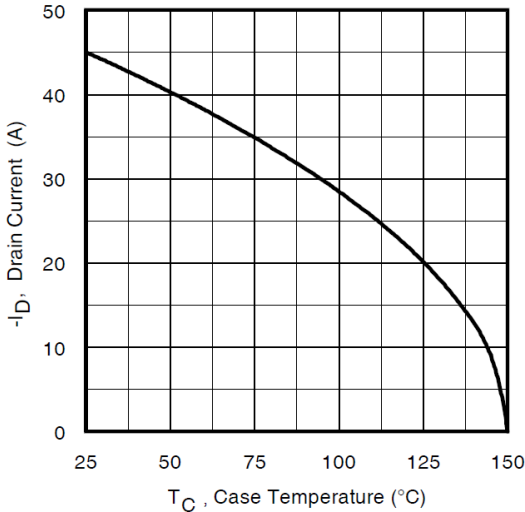


Fig 9. Maximum Drain Current Vs. Case Temperature

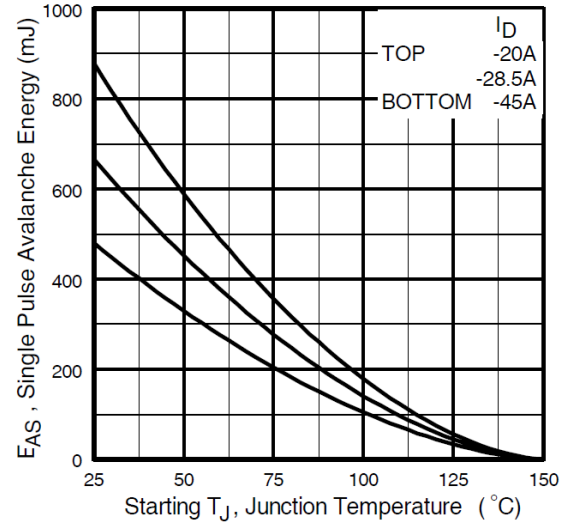


Fig 10. Maximum Avalanche Energy Vs. Drain Current

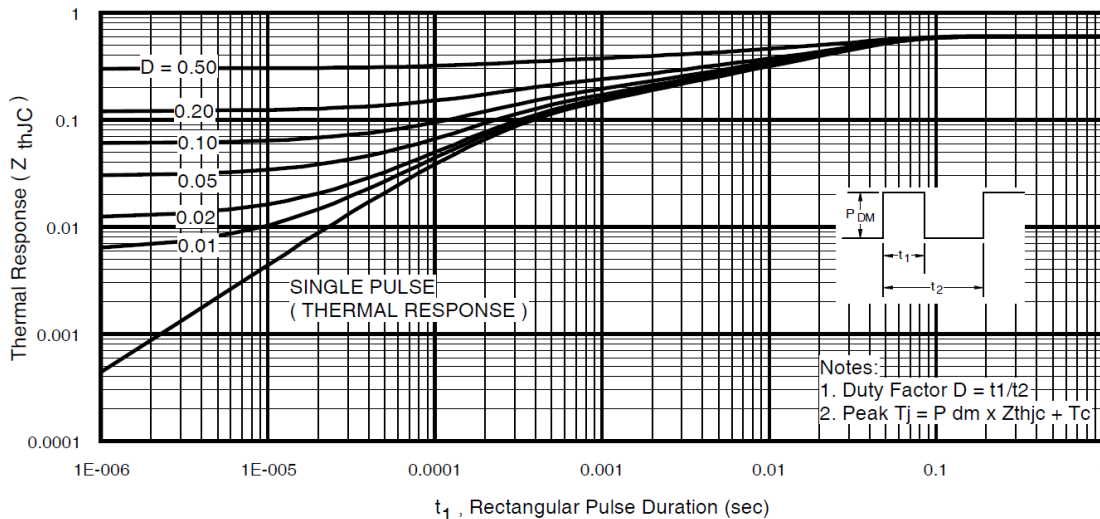


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

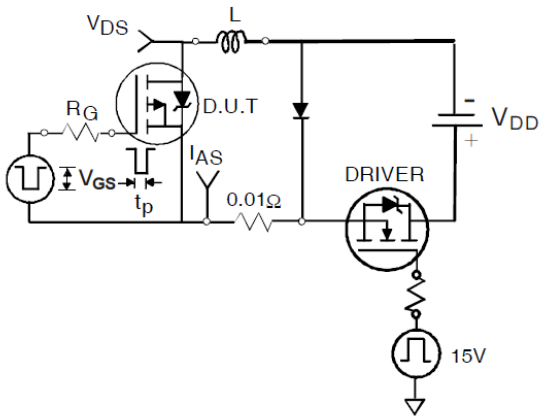


Fig 12a. Unclamped Inductive Test Circuit

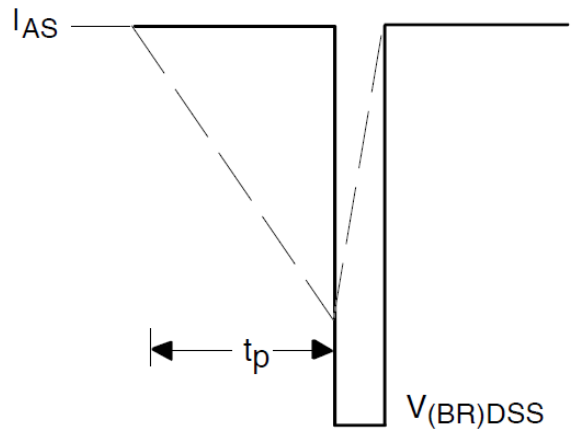


Fig 12b. Unclamped Inductive Wave-

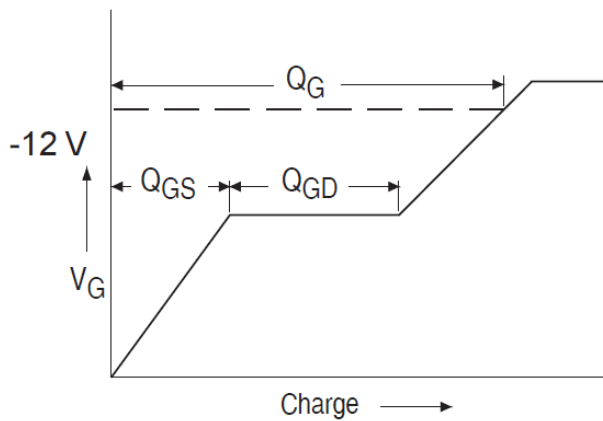


Fig 13a. Gate Charge Waveform

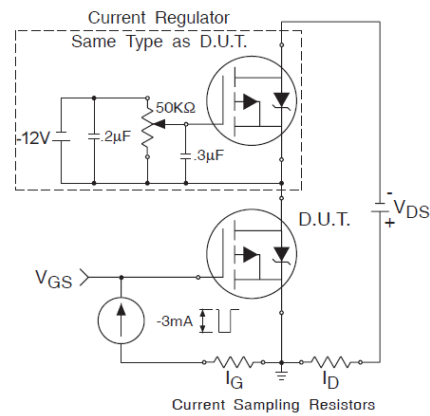


Fig 13b. Gate Charge Test Circuit

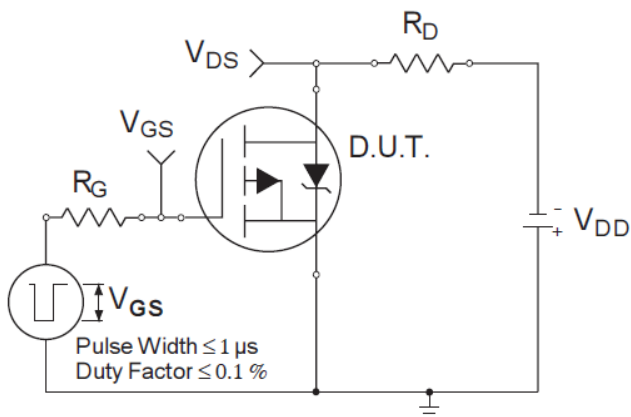


Fig 14a. Switching Time Test Circuit

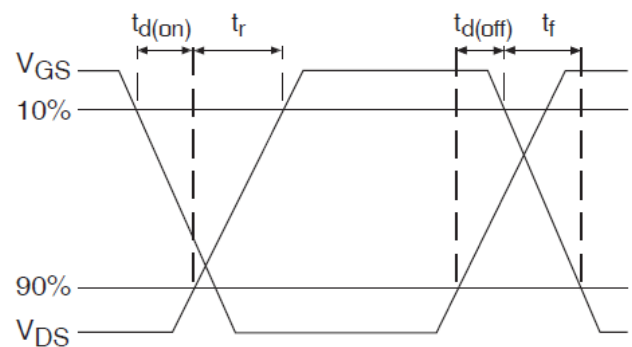
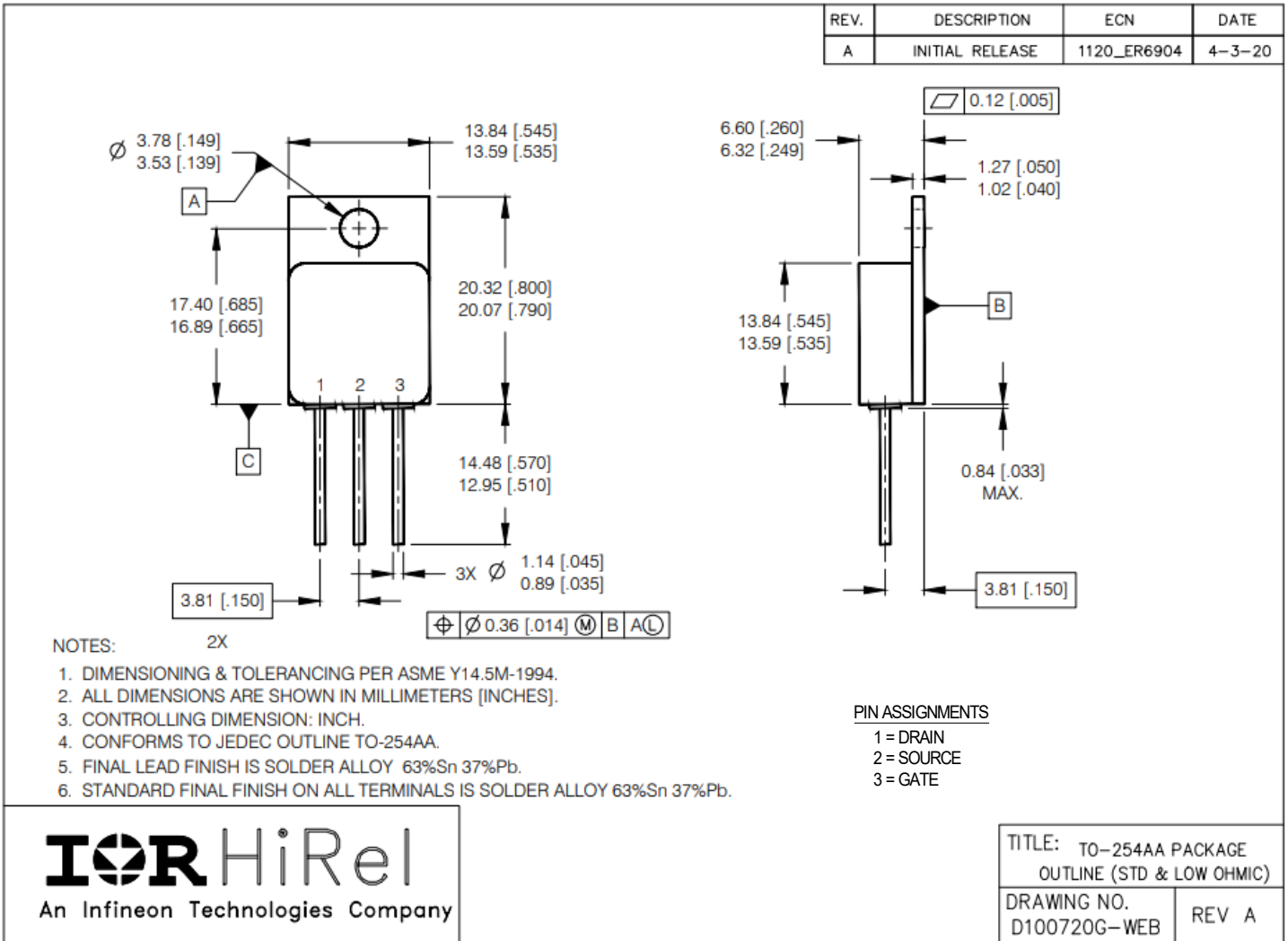


Fig 14b. Switching Time Waveforms

Note: For the most updated package outline, please see the website: [Low-Ohmic TO-254AA](http://www.infineon.com/lowohmic-to-254aa)

Case Outline and Dimensions - Low-Ohmic TO-254AA



BERYLLIA WARNING PER MIL-PRF-19500

Package containing beryllia shall not be ground, sandblasted, machined, or have other operations performed on them which will produce beryllia or beryllium dust. Furthermore, beryllium oxide packages shall not be placed in acids that will produce fumes containing beryllium.

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